SUM70090E

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Vishay Siliconix

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (А) с	Q _g (TYP.)	
100	0.0089 at V_{GS} = 10 V	50	33 nC	
100	0.0093 at V_{GS} = 7.5 V	50	33110	



Ordering Information:

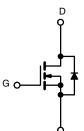
SUM70090E-GE3 (lead (Pb)-free and halogen-free)

FEATURES

- ThunderFET[®] power MOSFET
- Maximum 175 °C junction temperature
- Q_{gd} / Q_{gs} ratio < 1 optimizes switching characteristics
- 100 % $\rm R_g$ and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Power supply
 Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management



RoHS COMPLIANT

HALOGEN

FREE

N-Channe	MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	v
Gate-Source Voltage		V _{GS}	V _{GS} ± 20	
Continuous Drain Current (T 150 °C)	$T_{C} = 25 \ ^{\circ}C$		50 °	
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	I _D	50 ^c	A
Pulsed Drain Current (t = 100 µs)	I _{DM}	120	A	
Avalanche Current	I _{AS}	40		
Single Avalanche Energy ^a L = 0.1 mH		E _{AS}	80	mJ
Maximum Dawar Dissinction a	$T_{C} = 25 \ ^{\circ}C$	P	125	w
Maximum Power Dissipation ^a	T _C = 70 °C ^b	- P _D -	87.5	vv
Operating Junction and Storage Temperature F	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^b	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.2	0/11	

Notes

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR4 material).
- c. Package limited.

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS}=0~V,~I_D=250~\mu A$	100	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},\ I_D=250\ \mu A$	2	-	4	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 100 V, V_{GS} = 0 V, T_J = 125 $^\circ C$	-	-	150	μA	
		V_{DS} = 100 V, V_{GS} = 0 V, T_{J} = 175 $^{\circ}\text{C}$	-	-	5	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \! \geq \! 10 \text{ V}, V_{GS} \! = \! 10 \text{ V}$	50	-	-	А	
Drain Sauras On State Resistance a	Р	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.0074	0.0089	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	0.0077	0.0093		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 10 \text{ A}$	-	38	-	S	
Dynamic ^b	•						
Input Capacitance	C _{iss}		-	1950	-	pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 50 V, f = 1 MHz	-	845	-		
Reverse Transfer Capacitance	C _{rss}		-	54	-		
Total Gate Charge ^c	Qg		-	33	50	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	8.8	-		
Gate-Drain Charge ^c	Q _{gd}		-	7.5	-		
Gate Resistance	Rg	f = 1 MHz	0.7	3.5	7	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	30		
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 5 \Omega$	-	27	54		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{V}, \text{R}_g = 1 \Omega$	-	36	72	- ns	
Fall Time ^c	t _f		-	45	90		
Drain-Source Body Diode Ratings an	nd Characteri	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 µs)	I _{SM}		-	-	120	А	
Forward Voltage ^a	V _{SD}	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.5	V	
Reverse Recovery Time	t _{rr}		-	77	116	ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = -10 A, dl/dt = 100 A/µs	-	4.2	6.3	Α	
Reverse Recovery Charge	Q _{rr}		-	145	365	nC	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

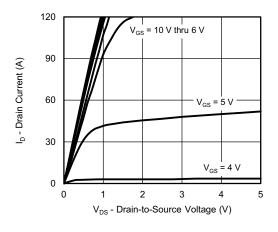
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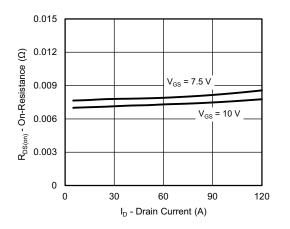
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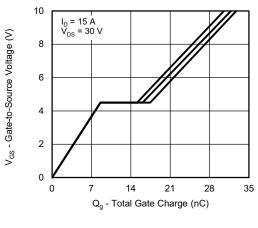
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



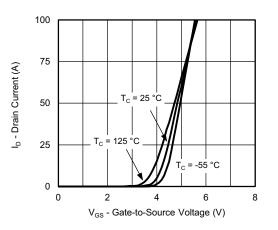
Output Characteristics



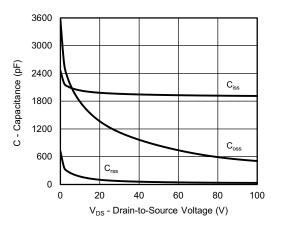
On-Resistance vs. Drain Current



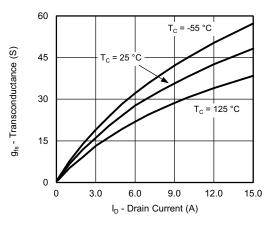
Gate Charge



Transfer Characteristics



Capacitance



Transconductance

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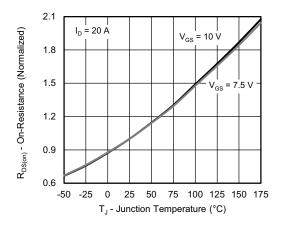
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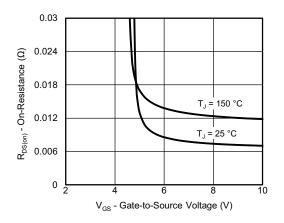
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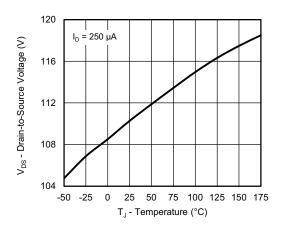
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



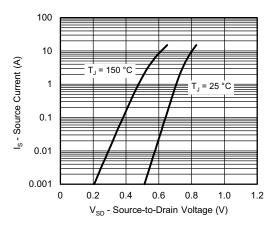
On-Resistance vs. Junction Temperature



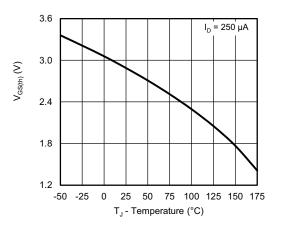
On-Resistance vs. Gate-to-Source Voltage



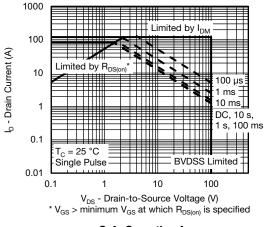
Drain Source Voltage vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage



Safe Operating Area

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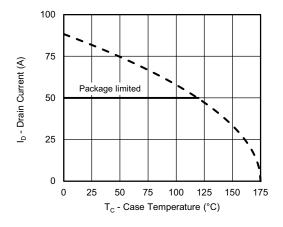
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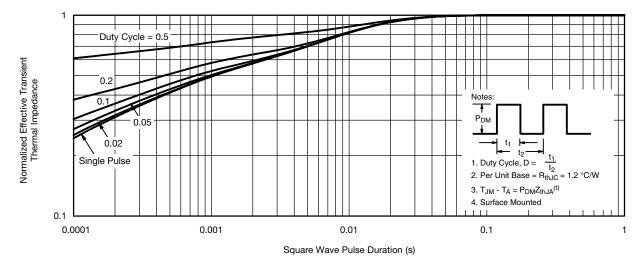


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Current De-Rating



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?64432.

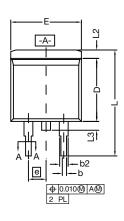
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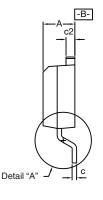


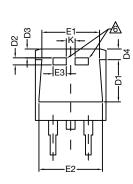
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TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

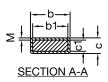








DETAIL A (ROTATED 90°)



		INCHES		MILLIN	IETERS
DIM.		MIN.	MAX.	MIN.	MAX.
	А	0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
с*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
е		0.100	BSC	2.54 BSC	
К		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		L2 0.040		1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010	BSC	0.254 BSC	
	М	-	0.002	-	0.050

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
- Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

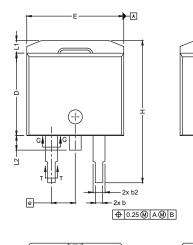
This feature is for thick lead.

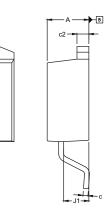
Revison: 28-Oct-2024

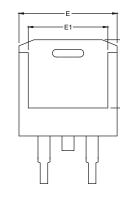


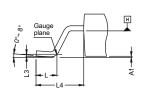
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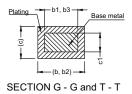
VERSION 2: FACILITY CODE = N











OPTION 1 2 leads



2

 \oplus

3 leads

DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
с	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
e	2.5	4 BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 typ.	
L4	4.78 5.28	
J1	2.56	2.96
ECN: S24-1080-Rev. L, 28-Oct-2024 DWG: 5843		



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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